FAIRCHILD SEMICONDUCTOR®

March 2013

FCH35N60

N-Channel SuperFET® MOSFET

600 V, 35 A, 98 mΩ

Features

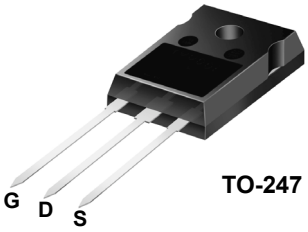
- 650 V @ T_J = 150°C
- Typ.$R_{DS(on)}$ = 79 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 139 nC)
- Low Effective Output Capacitance (Typ. C_{oss}.eff = 340 pF)
- 100% Avalanche Tested

Application

- Solar Inverter
- AC-DC Power Supply

Description

SuperFET® MOSFET is Fairchild Semiconductor®'s first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.



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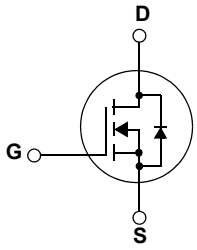


MOSFET Maximum Ratings T_C = 25°C unless otherwise noted*

Symbol	Parameter			FCH35N60	Unit
V_{DSS}	Drain to Source Voltage			600	V
V_{GSS}	Gate-Soure voltage			±30	V
I_D	Drain Current	-Continuous (T_C = 25°C)		35	A
		-Continuous (T_C = 100°C)		22.2	
I_{DM}	Drain Current	- Pulsed	(Note 1)	105	A
E_{AS}	Single Pulsed Avalanche Energy		(Note 2)	1455	mJ
I_{AR}	Avalanche Current		(Note 1)	35	A
E_{AR}	Repetitive Avalanche Energy		(Note 1)	31.25	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	20	V/ns
P_D	Power Dissipation	(T_C = 25°C)		312.5	W
		- Derate above 25°C		2.5	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range			-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	-	0.4	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Heat Sink	0.24	-	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	42	

Package Marking and Ordering Information $T_C = 25^oC$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCH35N60	FCH35N60	TO-247	-	-	30

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V, T_J = 25°C	600	-	-	V
		I_D = 250 μA, V_{GS} = 0 V, T_J = 150°C	-	650	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.6	-	V/°C
BV_{DS}	Drain-Source Avalanche Breakdown Voltage	V_{GS} = 0 V, I_D = 16 A	-	700	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 600 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 480 V, T_C = 125°C	-	-	10	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 17.5 A	-	0.079	0.098	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 17.5 A	-	28.8	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	-	4990	6640	pF
C_{oss}	Output Capacitance		-	2380	3170	pF
C_{rss}	Reverse Transfer Capacitance		-	140	-	pF
C_{oss}	Output Capacitance	V_{DS} = 480 V, V_{GS} = 0 V, f = 1.0 MHz	-	113	-	pF
C_{oss} eff.	Effective Output Capacitance	V_{DS} = 0 V to 480 V, V_{GS} = 0 V	-	340	-	pF
Q_g	Total Gate Charge at 10V	V_{DS} = 480 V, I_D = 35 A, V_{GS} = 10 V (Note 4)	-	139	181	nC
Q_{gs}	Gate to Source Gate Charge		-	31	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	69	-	nC
ESR	Equivalent Series Resistance (G-S)	Drain Open, F= 1 MHZ	-	1.4	-	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 300 V, I_D = 35 A, R_G = 4.7 Ω (Note 4)	-	34	78	ns
t_r	Turn-On Rise Time		-	120	250	ns
$t_{d(off)}$	Turn-Off Delay Time		-	105	220	ns
t_f	Turn-Off Fall Time		-	73	155	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	35	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	105	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 35 A	-	-	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 35 A, dI_F/dt = 100 A/μs	-	614	-	ns
Q_{rr}	Reverse Recovery Charge		-	16.3	-	μC

Notes:
1: Repetitive Rating: Pulse width limited by maximum junction temperature
2: I_{AS} = 17.5 A, V_{DD} = 50 V, R_G = 25 Ω, Starting T_J = 25°C
3: I_{SD} ≤ 35 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4: Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

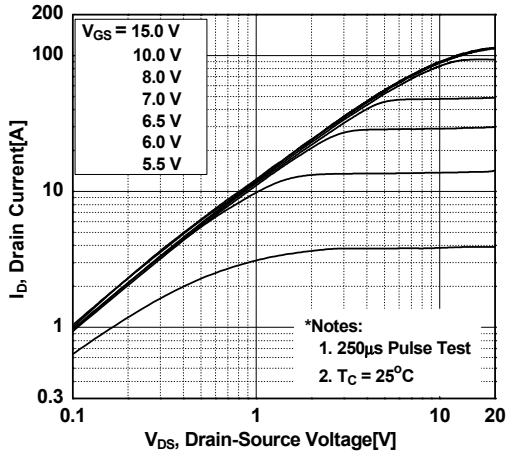


Figure 2. Transfer Characteristics

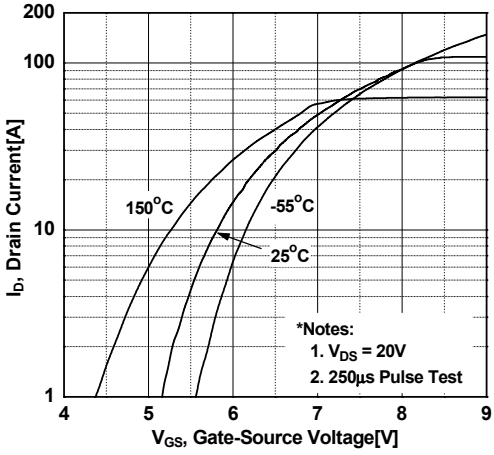


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

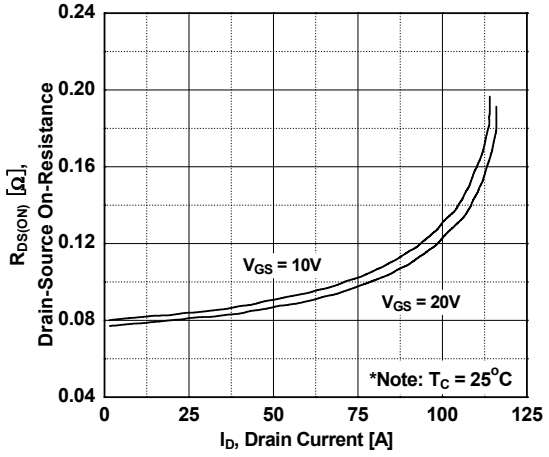


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

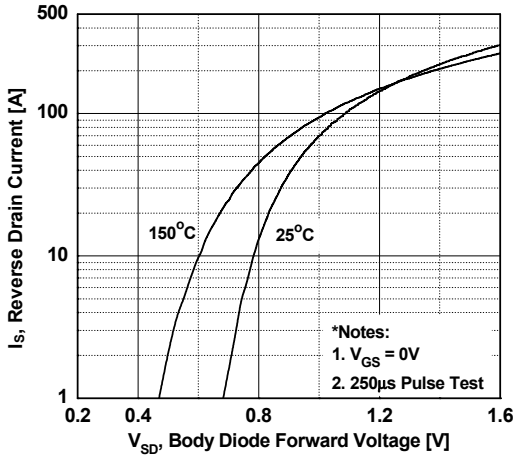


Figure 5. Capacitance Characteristics

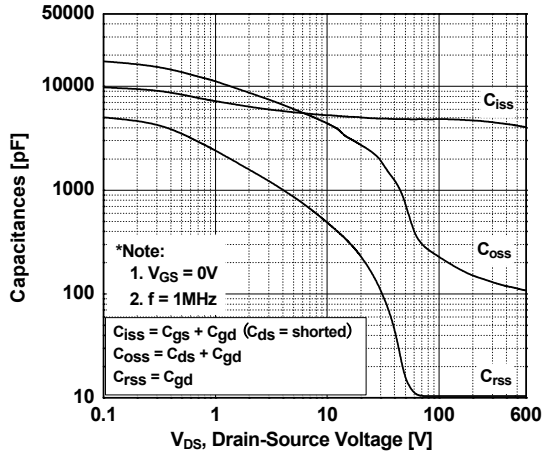
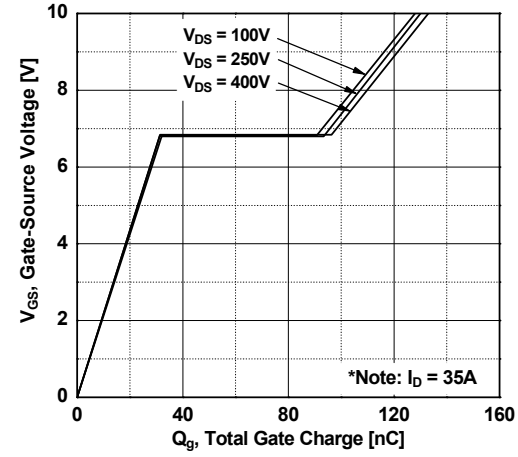


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

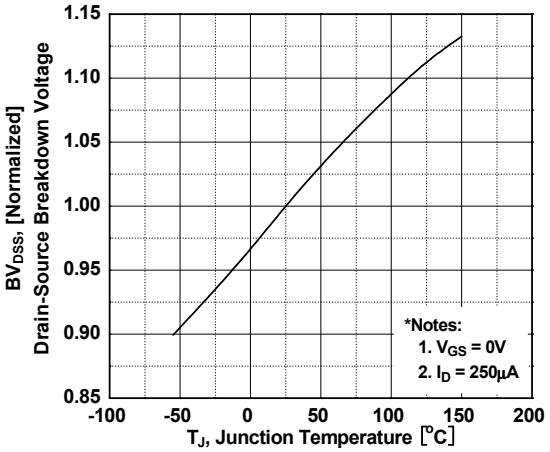


Figure 8. On-Resistance Variation vs. Temperature

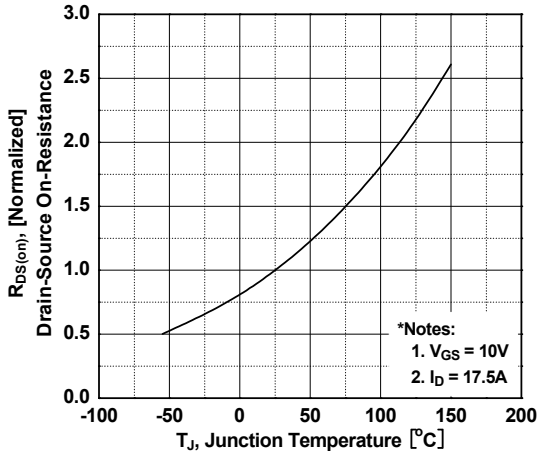


Figure 9. Maximum Safe Operating Area

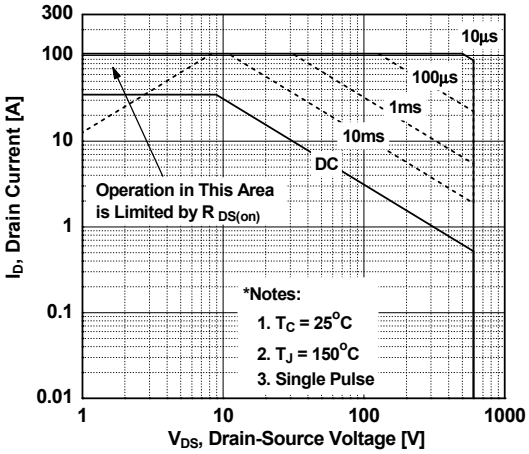


Figure 10. Maximum Drain Current vs. Case Temperature

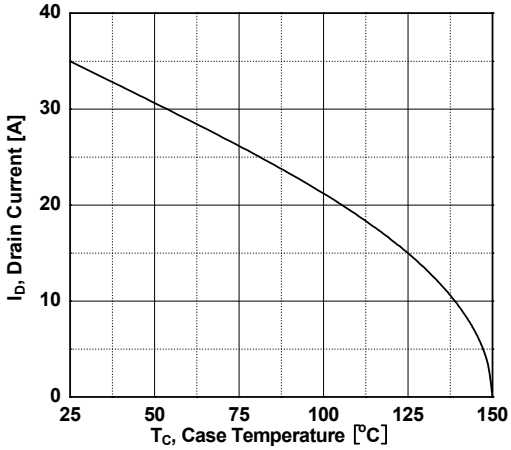
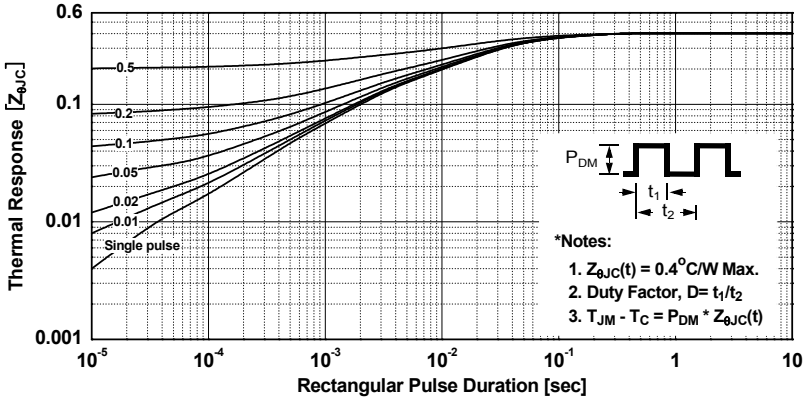
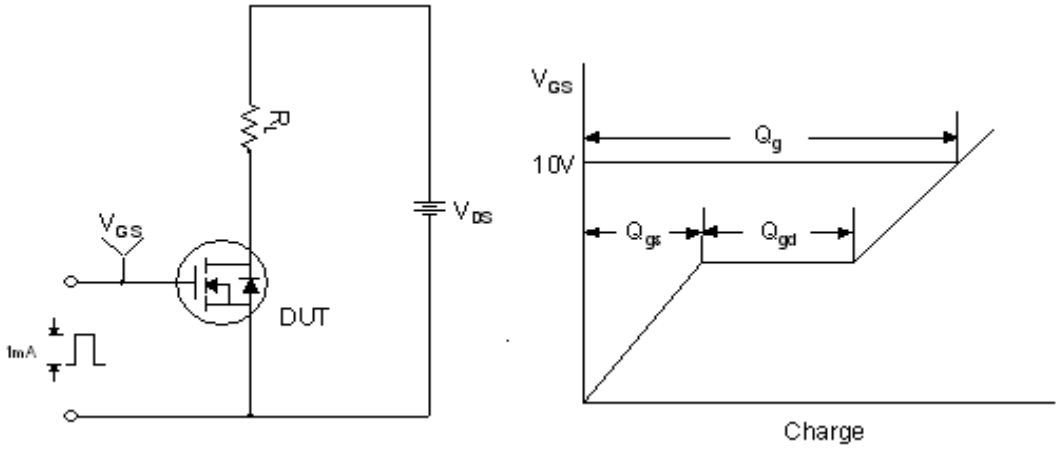


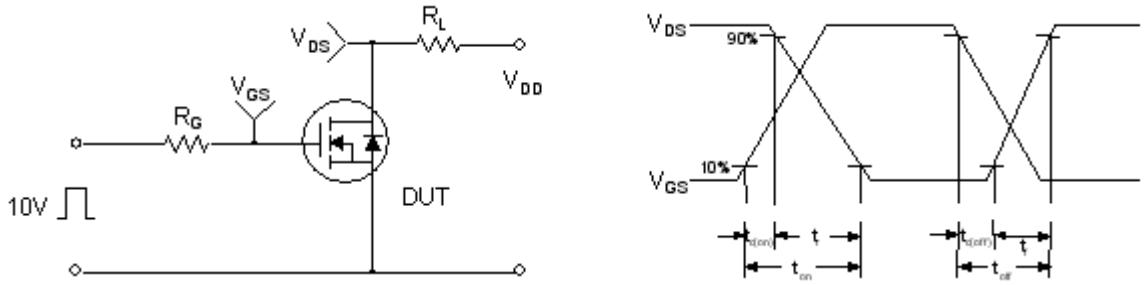
Figure 11. Transient Thermal Response Curve



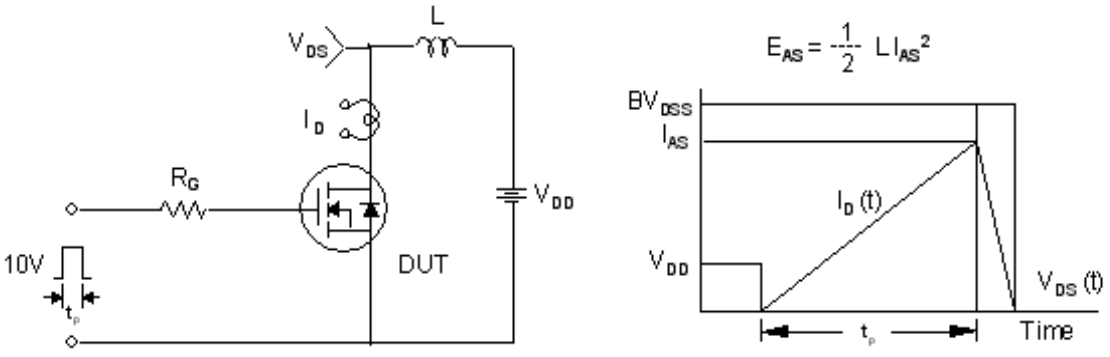
Gate Charge Test Circuit & Waveform



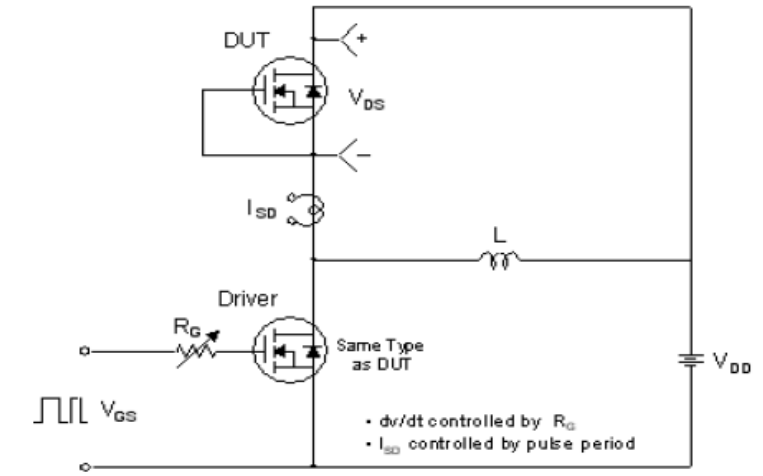
Resistive Switching Test Circuit & Waveforms

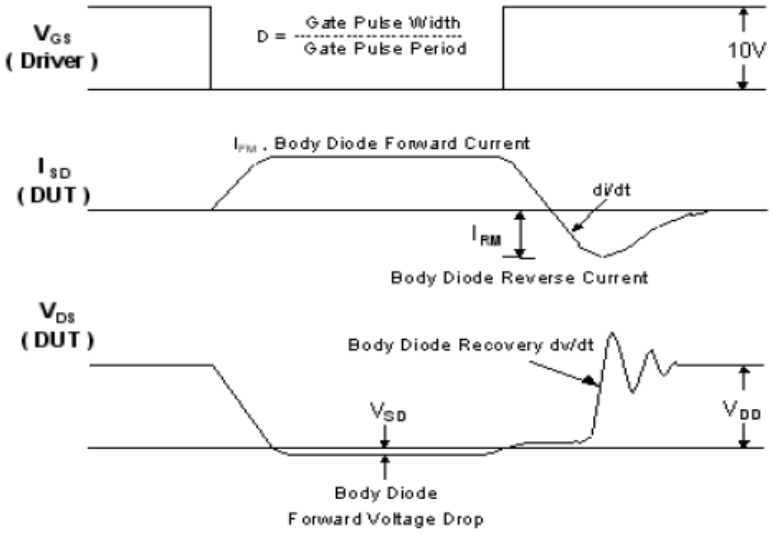


Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms





Mechanical Dimensions

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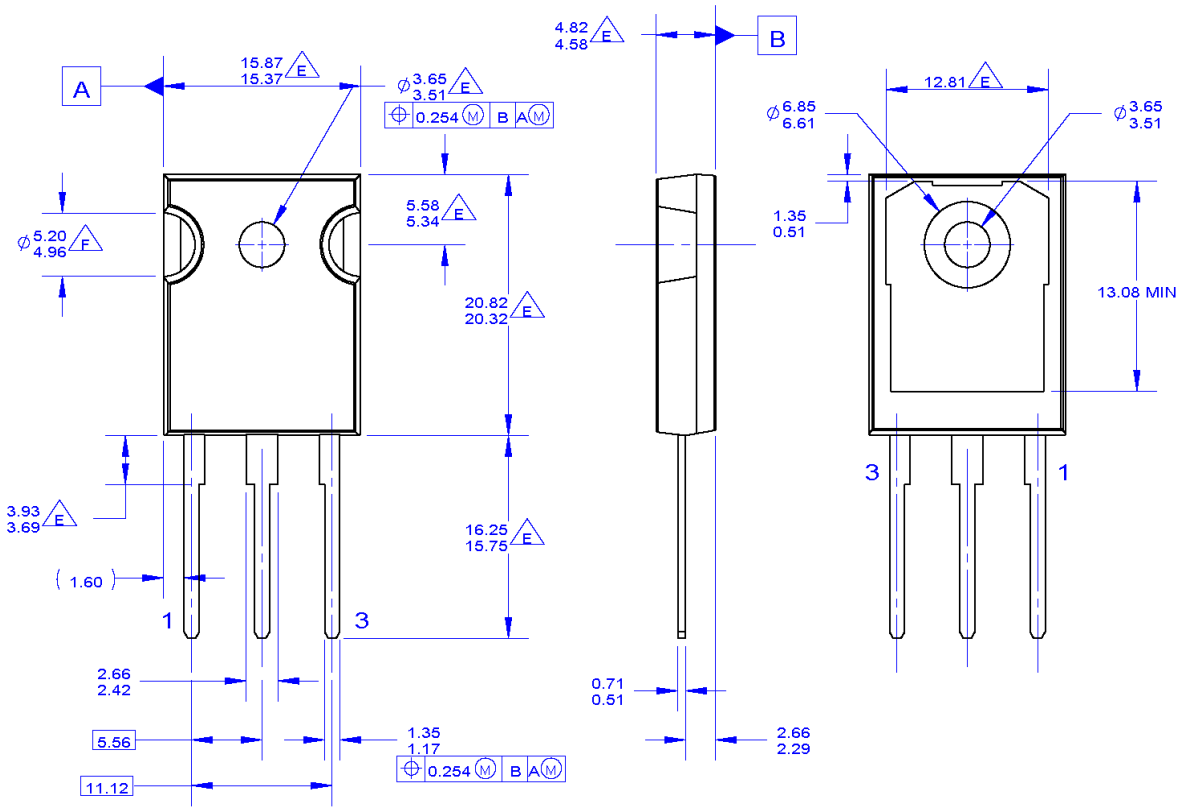

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Dimensions in Millimeters

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